FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.: ASC-001C1 APPLICANT(S): Hammond *et al.* SERIAL NO.: 10/688,003 FILING DATE: October 17, 2003 GROUP: ~~Not yet assigned~~ 2811

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	A6	5,877,056	03/02/1999	Wu *et al.*	—	—	
	A7	6,040,208	03/21/2000	Honeycutt *et al.*	—	—	
	A8	6,284,615	09/04/2001	Pinto *et al.*	—	—	
	A9	6,310,367	10/30/2001	Yagishita *et al.*	—	—	
	A10	6,313,016	11/06/2001	Kibbel *et al.*	—	—	
	A11	6,448,840	09/10/2002	Kao *et al.*	—	—	
RKH	A12	6,680,496	01/20/2004	Hammond *et al.*	257	192	07/08/2002

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	~~A17~~	~~2002/0123183~~	~~09/05/2002~~	~~Fitzgerald~~			
	~~A18~~	~~2002/0125497~~	~~09/12/2002~~	~~Fitzgerald~~			
	~~A19~~	~~2003/0013323~~	~~01/16/2003~~	~~Hammond *et al.*~~			
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	A40	6,271,726	08/07/2001	Fransis *et al.*	—	—	
	A41	6,555,839 ✓	04/29/2003	Fitzgerald	257	19	
	A42	6,583,015	06/24/2003	Fitzgerald *et al.*	—	—	
	A43	6,593,191	07/15/2003	Fitzgerald	—	—	
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KMG	A45	6,646,322	11/11/2003	Fitzgerald	—	—	07/16/2001

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	~~B3~~	~~02/071488 A1~~	~~09/12/2002~~	~~WO~~				~~N~~	~~Y~~
	~~B4~~	~~02/071491 A1~~	~~09/12/2002~~	~~WO~~				~~N~~	~~Y~~
	~~B5~~	~~02/071493 A2~~	~~09/12/2002~~	~~WO~~				~~N~~	~~Y~~
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EXAMINER G. MUNSON	DATE CONSIDERED 25 JUNE 2004

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.: ASC-001C1 APPLICANT(S): Hammond *et al.* SERIAL NO.: 10/688,003 FILING DATE: October 17, 2003 GROUP: 2811

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EXAMINER	G. MUNSON	DATE CONSIDERED	25 JUNE 2004

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